

1 **IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

2 Application Serial No. 09/298,160
3 Filing Date April 22, 1999
4 Inventor Dan G. Custer et al.
5 Assignee Micron Technology, Inc.
6 Group Art Unit 1746
7 Examiner A. Olsen
8 Attorney's Docket No. MI22-1172
9 Title: Polishing Systems, Methods of Polishing Substrates, and Methods of Preparing
10 Liquids for Semiconductor Fabrication Processes
11

12 **RESPONSE TO MAY 15, 2000 OFFICE ACTION**

13 To: Assistant Commissioner for Patents
14 Washington, D.C. 20231

15 From: Bernard Berman (Tel. 509-624-4276; Fax 509-838-3424)
16 Wells, St. John, Roberts, Gregory & Matkin P.S.
17 601 W. First Avenue, Suite 1300
18 Spokane, WA 99201-3828

19 Sir:

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Sir:

Responsive to the Office Action dated May 15, 2000, applicant requests reconsideration of the above referenced application in view of the amendments and remarks that follow [unless otherwise indicated, deletions are bracketed, additions are underlined]:

AMENDMENTS

Please amend Claim 1 as follows:

1. (Amended) A method of preparing a liquid for a semiconductor fabrication process comprising:

providing a liquid;

degassifying the liquid; [and]

injecting a gas into the liquid to regassify the liquid, the regassification increasing [increase] a total dissolved gas concentration in the liquid to greater than or equal to 200 ppb, and

employing the liquid having the increased total dissolved gas concentration for the semiconductor process.